

Effect of Solution Composition on the Morphology of Synthesized β -Ga₂O₃ Particles

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Abstract. Micro- and nanoparticles of β -Ga₂O₃ are synthesized as a result of chemical reaction of an aqueous solution of gallium nitrate and various alkalis: ammonia, sodium, potassium, and lithium hydroxides. It is shown that particles morphology depends on the type and concentration of alkali. The use of microwave treatment of ammonia containing solutions made it possible to change the shape of particles from ellipsoidal to parallelepiped while maintaining their size. In contrast to the synthesis with ammonia, for other alkalis dispersed particles were obtained only at a ratio of alkali to gallium nitrate equal to 3, and these particles did not belong to the gallium oxide β -phase.

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REFERENCES

- [1] Y. Liu, L. Du, G. Liang, W. Mu, Z. Jia, M. Xu, Q. Xin, X. Tao, A. Song, *Ga₂O₃ field-effect-transistor-based solar-blind photodetector with fast response and high photo-to-dark current ratio*, IEEE Electron Device Letters, 2018, vol. 39, no. 11, pp. 1696–1699.
- [2] M. Higashiwaki, *β-Ga₂O₃ material properties, growth technologies, and devices: a review*, AAPPS Bulletin, 2022, vol. 32, art. no. 3.
- [3] E. Ahmadi, Y. Oshima, *Materials issues and devices of α- and β-Ga₂O₃*, Journal of Applied Physics, 2019, vol. 126, no. 16, art. no. 160901.
- [4] D.I. Panov, V.A. Spiridonov, D.A. Zakgeim, A.V. Kremleva, D.A. Bauman, A.E. Romanov, V.E. Bougrov, *Growth technology and optical properties of bulk crystalline gallium oxide*, Reviews on Advanced Materials and Technologies, 2020, vol. 2, no. 3, pp. 51–55.
- [5] A.A. Petrenko, Ya.N. Kovach, D. A. Bauman, M.A. Odnoblyudov, V.E. Bougrov, A.E. Romanov, *Current state of Ga₂O₃ based electronic and optoelectronic devices. Brief review*, Reviews on Advanced Materials and Technologies, 2021, vol. 3, no. 2, pp. 1–26.
- [6] S. Stepanov, V.I. Nikolaev, V.E. Bougrov, A.E. Romanov, *Gallium oxide: properties and applications - a review*, Reviews on Advanced Materials Science, 2016, vol. 44, no. 1, pp. 63–86.
- [7] G. Irudayadass, *Estimation of ionization coefficients of gallium oxide for the purpose of TCAD simulation*, Thesis, University of Illinois at Chicago, 2018.
- [8] E. Chikoidze, A. Fellous, A. Perez-Tomas, G. Sauthier, T. Tchelidze, C. Ton-That, T.T. Huynh, M. Phillips, S. Russell, M. Jennings, B. Berini, F. Jomard, Y. Dumont, *P-type β-gallium oxide: a new perspective for power and optoelectronic devices*, Materials Today Physics, 2017, vol. 3, pp. 118–126.
- [9] R. Roy, V.G. Hill, E.F. Osborn, *Polymorphism of Ga₂O₃ and the system Ga₂O₃—H₂O*, Journal of the American Chemical Society, 1952, vol. 74, no. 3, pp. 719–722.
- [10] X.T. Zhou, F. Heigl, J.Y.P. Ko, M.W. Murphy, J.G. Zhou, T. Regier, R.I.R. Blyth, T.K. Sham, *Origin of luminescence from Ga₂O₃ nanostructures studied using x-ray absorption and luminescence spectroscopy*, Physical Review B, 2007, vol. 75, no. 12, art. no. 125303.
- [11] A.Yu. Ivanov, A.V. Kremleva, Sh.Sh. Sharofidinov, *The electrical properties of schottky barrier diode structures based on hve grown sn doped Ga₂O₃ layers*, Reviews on Advanced Materials and Technologies, 2022, vol. 4, no. 1, pp. 33–38.
- [12] A.M. Smirnov, A.Yu. Ivanov, A.V. Kremleva, Sh.Sh. Sharofidinov, A.E. Romanov, *Stress relaxation due to dislocation formation in orthorhombic Ga₂O₃ films grown on Al₂O₃ substrates*, Reviews on Advanced Materials and Technologies, 2022, vol. 4, no. 3, pp. 1–6.
- [13] J. Lee, H. Kim, L. Gautam, M. Razeghi, *High thermal stability of k-Ga₂O₃ grown by MOCVD*, Crystals, 2021, vol. 11, no. 4, art. no. 446.
- [14] H.H. Tippins, *Optical absorption and photoconductivity in the band edge of β-Ga₂O₃*, Physical Review, 1965, vol. 140, no. 1A, pp. A316–A319.
- [15] D.I. Panov, Z. Xi, V.A. Spiridonov, L.V. Azina, R.K. Nuryev, N.D. Prasolov, L.A. Sokura, D.A. Bauman, V.E. Bougrov, *Spray-pyrolysis fabrication and quality study of β-Ga₂O₃ thin films*, Reviews on Advanced Materials and Technologies, 2021, vol. 3, no. 4, pp. 7–12.
- [16] Z. Xu, J. Zang, X. Yang, Y. Chen, Q. Lou, K. Li, C. Lin, Z. Zhang, C. Shan, *Zero-biased solar-blind photodetectors based on AlN/β-Ga₂O₃ heterojunctions*, Semiconductor Science and Technology, 2021, vol. 36, no. 6, art. no. 065007.
- [17] L.S. Reddy, Y.H. Ko, J.S. Yu, *Hydrothermal synthesis and photocatalytic property of β-Ga₂O₃ nanorods*, Nanoscale Research Letters, 2015, vol. 364, no. 10, art. no. 364.
- [18] Y.H. Choi, K.H. Baik, S. Kim, J. Kim, *Photoelectrochemical etching of ultra-wide bandgap β-Ga₂O₃ semiconductor in phosphoric acid and its optoelectronic device application*, Applied Surface Science, 2021, vol. 539, art. no. 148130.
- [19] Y. Hou, L. Wu, X. Wang, Z. Ding, Z. Li, X. Fu, *Photocatalytic performance of α-, β-, and γ-Ga₂O₃ for the destruction of volatile aromatic pollutants in air*, Journal of Catalysis, 2007, vol. 250, no. 1, pp. 12–18.
- [20] E. Jang, J.-H. Won, S.-J. Hwang, J.-H. Choy, *Fine tuning of the face orientation of ZnO crystals to optimize their photocatalytic activity*, Advanced Materials, 2006, vol. 18, no. 24, pp. 3309–3312.
- [21] B. Zheng, W. Hua, Y. Yue, Z. Gao, *Dehydrogenation of propane to propene over different polymorphs of gallium oxide*, Journal of Catalysis, 2005, vol. 232, no. 1, pp. 143–151.

- [22] I.M. Sosnin, L.A. Sokura, M.V. Dorogov, I.G. Smirnova, A.E. Romanov, *Aqueous solution synthesis and size control of acid-resistant β -Ga₂O₃ microparticles*, *Materials Letters*, 2023, vol. 335, art. no. 133758.
- [23] B. Alhalaili, H. Mao, S. Islam, *Ga₂O₃ nanowire synthesis and device applications*, in: G.Z. Kyzas, A.C. Mitropoulos (eds.), *Novel Nanomaterials — Synthesis and Applications*, InTech, 2018.

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